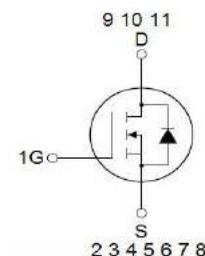
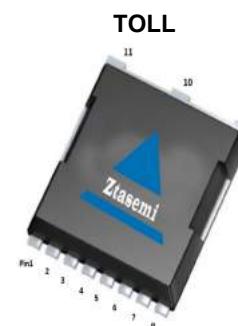




Features

- N-Channel
- Low grid charge
- Low reverse transmission capacitance
- Fast switching speed
- Pb-free lead plating
- 100% EAS Tested

V_{DS}	40	V
$R_{DS(on),TYP}$ @ $V_{GS}=10$ V	0.8	mΩ
I_D	250	A



Part ID	Package Type	Marking	Packing
ZTG008N04L	TOLL	ZTG008N04L	2000pcs/Reel

Absolute Maximum Ratings $T_A = 25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter	Rating	Unit	
Common Ratings ($T_c=25^\circ\text{C}$ Unless Otherwise Noted)				
V_{GS}	Gate-Source Voltage	± 20	V	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	40	V	
T_J	Maximum Junction Temperature	175	°C	
T_{STG}	Storage Temperature Range	-55 to 175	°C	
I_{DM}	Drain Current-Continuous@ Current-Pulsed	$T_c=25^\circ\text{C}$	1000	A
Mounted on Large Heat Sink				
I_D	Drain Current-Continuous	$T_c=25^\circ\text{C}$	250	A
		$T_c=100^\circ\text{C}$	170	A
P_D	Maximum Power Dissipation	300	W	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	0.5	°C/W	
Drain-Source Avalanche Ratings				
EAS	Avalanche Energy, Single Pulsed (Note 1)	1690	mJ	



Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ $T_J=25^\circ\text{C}$ (unless otherwise stated)						
V(BR)DSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	40	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=40\text{V}, V_{GS}=0\text{V}$	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$	--	--	± 100	nA
V _{G(th)}	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	2.3	--	3.6	V
R _{D(on)}	Drain-Source On-State Resistance	$V_{GS}=10\text{V}, I_D=100\text{A}$	--	0.8	0.95	$\text{m}\Omega$
Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)						
C _{iss}	Input Capacitance	$V_{DS}=20\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$	--	5786	--	pF
C _{oss}	Output Capacitance		--	2217	--	pF
C _{rss}	Reverse Transfer Capacitance		--	68	--	pF
Q _g	Total Gate Charge	$V_{DS}=20\text{V}, I_D=100\text{A}, V_{GS}=10\text{V}$	--	90	--	nC
Q _{gs}	Gate-Source Charge		--	29	--	nC
Q _{gd}	Gate-Drain Charge		--	18	--	nC
Switching Characteristics (Note 2)						
T _{d(on)}	Turn-on Delay Time	$V_{DD}=20\text{V}, I_D = 100\text{A}, R_G=1.6\Omega, V_{GS}=10\text{V}$	--	14	--	ns
T _r	Turn-on Rise Time		--	7.5	--	ns
T _{d(off)}	Turn-Off Delay Time		--	56	--	ns
T _f	Turn-Off Fall Time		--	9.8	--	ns
Source-Drain Diode Characteristics@ $T_J = 25^\circ\text{C}$ (unless otherwise stated)						
I _s	Diode Forward Current		--	--	250	A
V _{SD}	Forward on voltage	$I_s=100\text{A}, V_{GS}=0\text{V}$	--	--	1.2	V
T _{rr}	Reverse Recovery Time	$T_J=25^\circ\text{C}, I_s=100\text{A}, \frac{di}{dt}=100\text{A}/\mu\text{s}$	--	38	--	ns
Q _{rr}	Reverse Recovery Charge		--	125	--	nC

Notes:

1. EAS condition : $T_J=25^\circ\text{C}, V_{DD}=20\text{V}, V_G=10\text{V}, L=0.5\text{mH}, R_G=25\Omega$

2. Guaranteed by design, not subject to production

3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink k , assuming a maximum junction temperature of $T_J(\text{MAX})=175^\circ\text{C}$. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

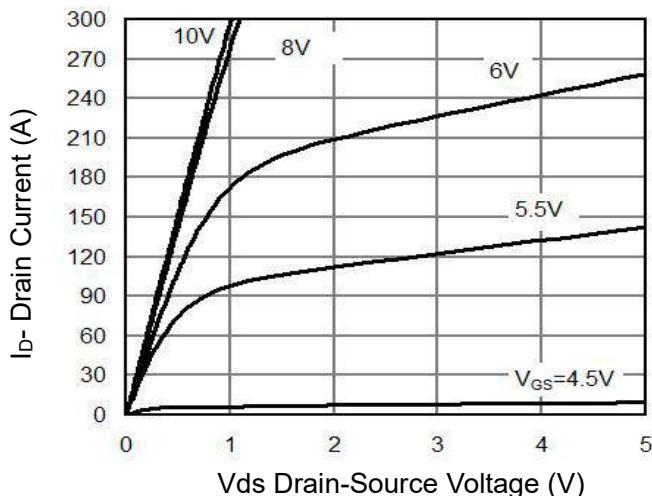


Figure 1 Output Characteristics

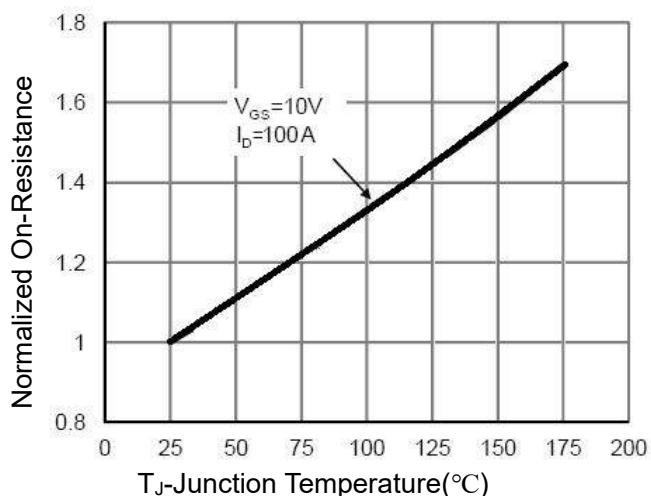


Figure 4 Rdson-Junction Temperature

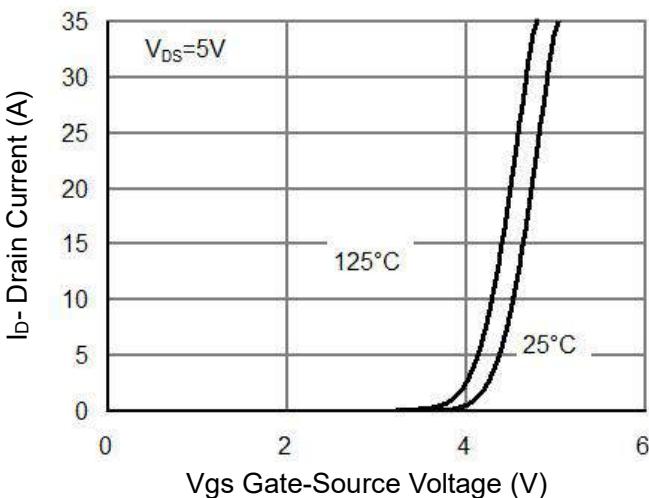


Figure 2 Transfer Characteristics

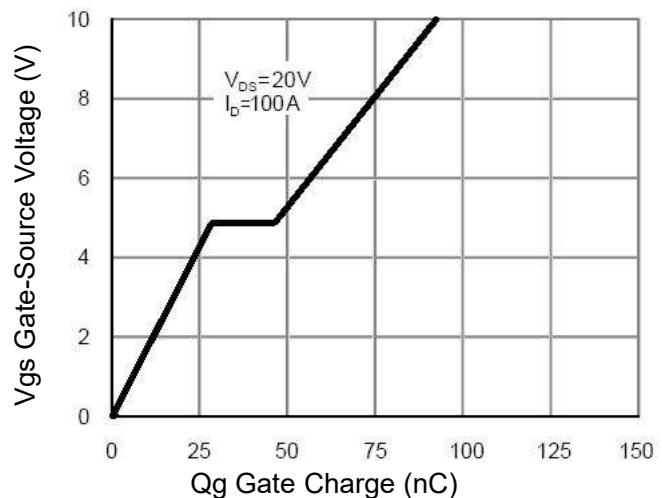


Figure 5 Gate Charge

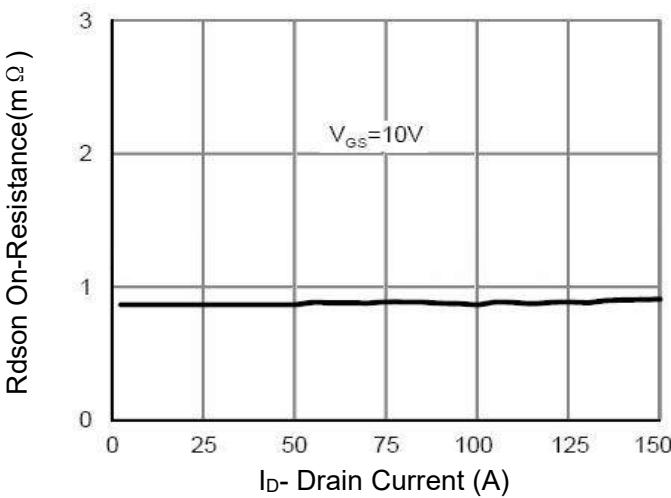


Figure 3 Rdson- Drain Current

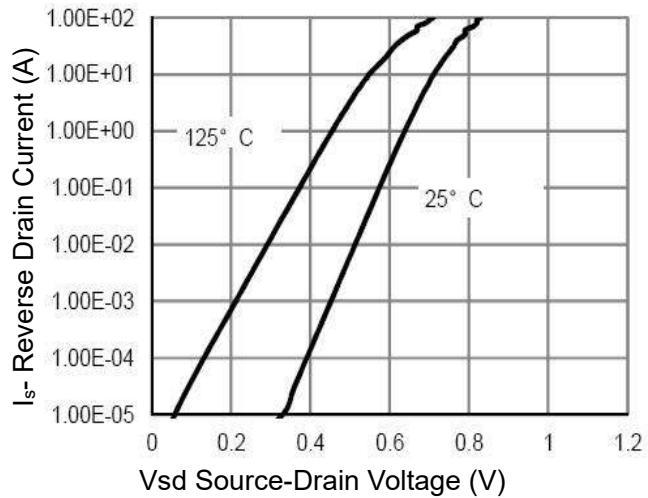


Figure 6 Source- Drain Diode Forward

Typical Electrical and Thermal Characteristics

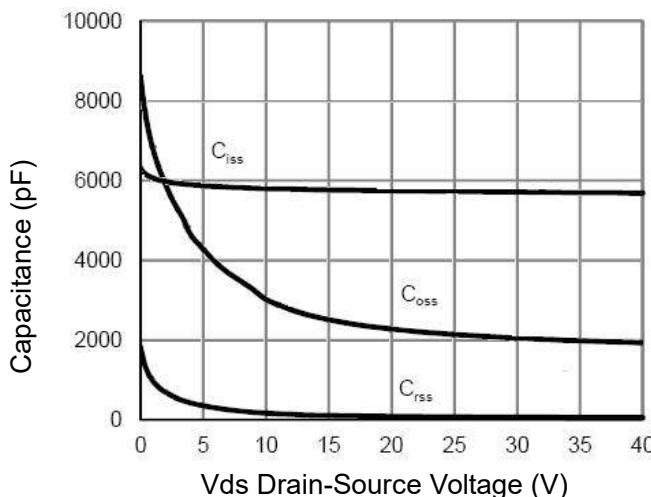


Figure 7 Capacitance vs Vds

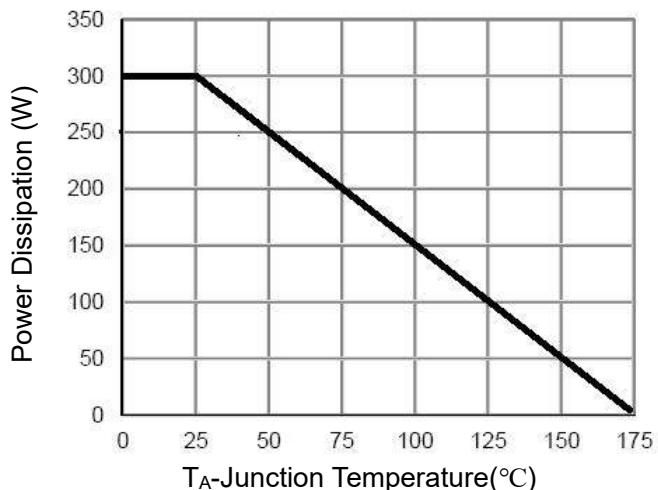


Figure 9 Power De-rating

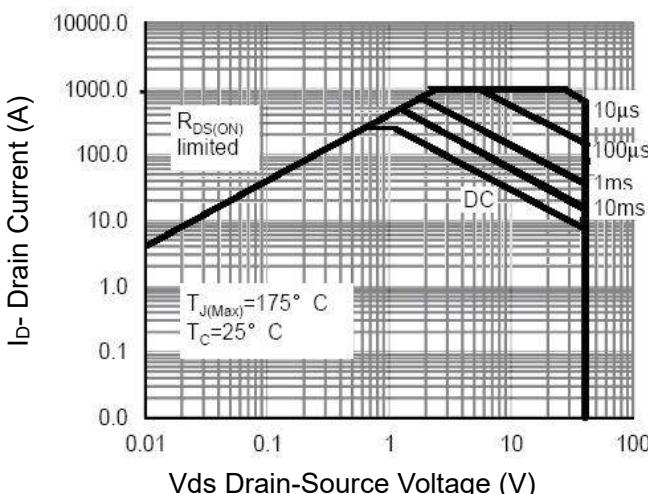


Figure 8 Safe Operation Area ^(Note3)

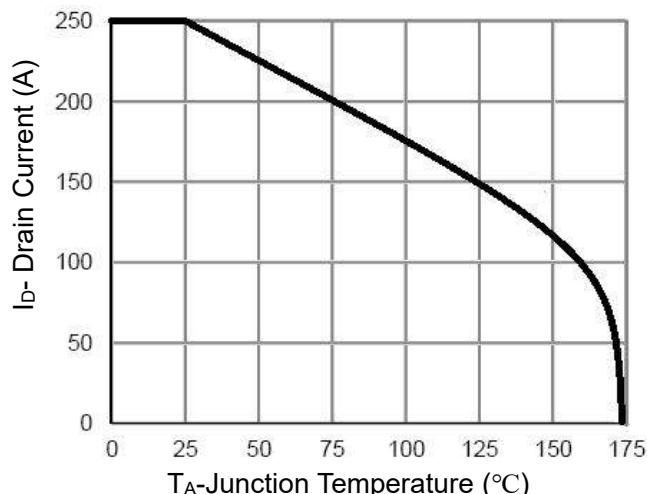


Figure 10 Current De-rating

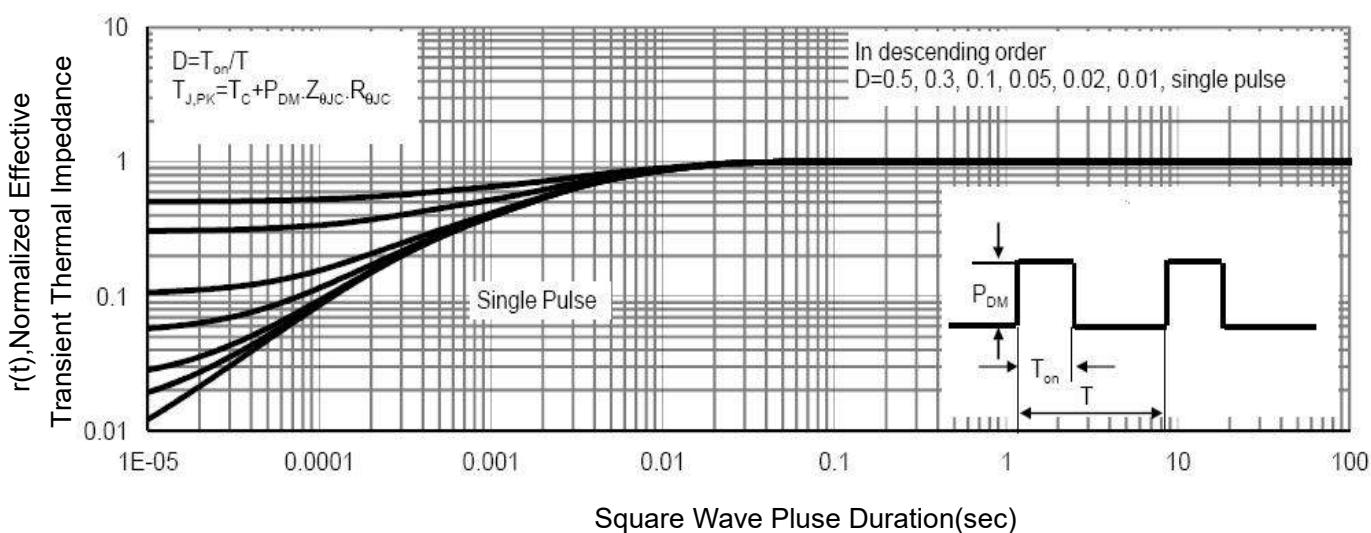
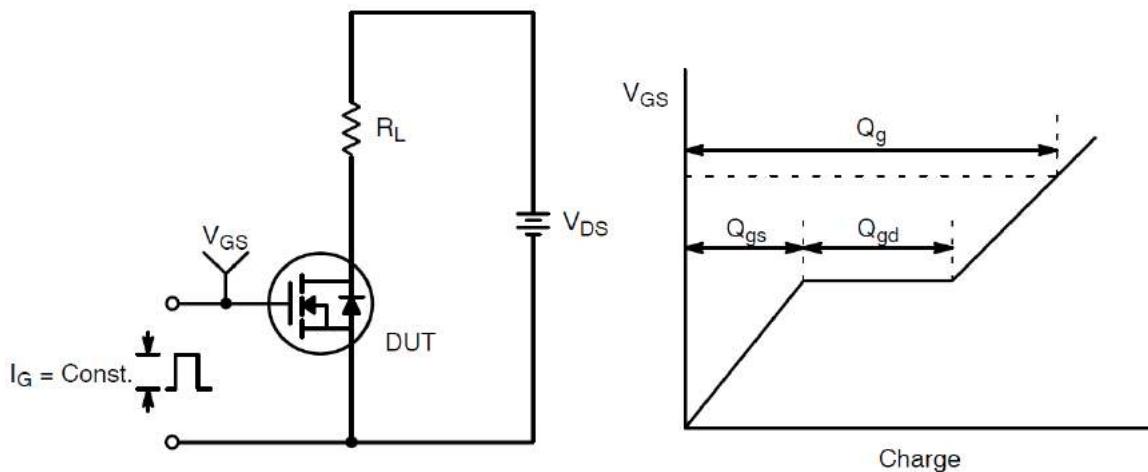
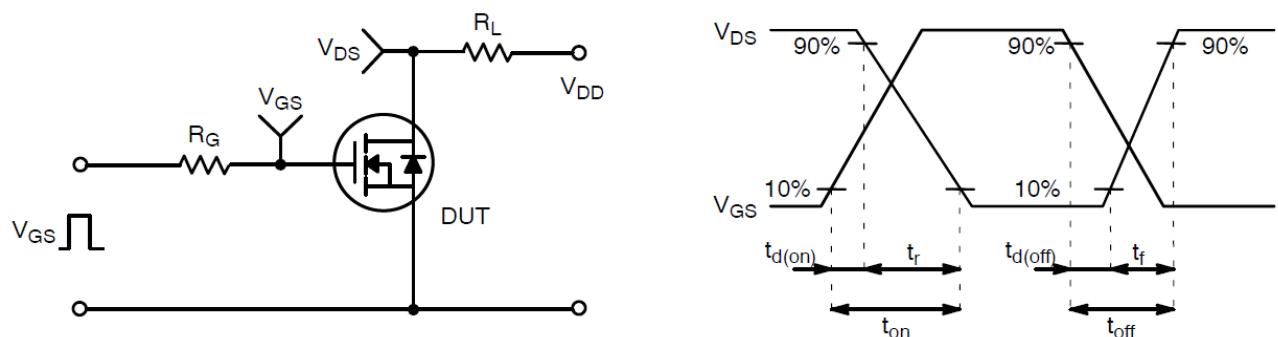


Figure 11 Normalized Maximum Transient Thermal Impedance

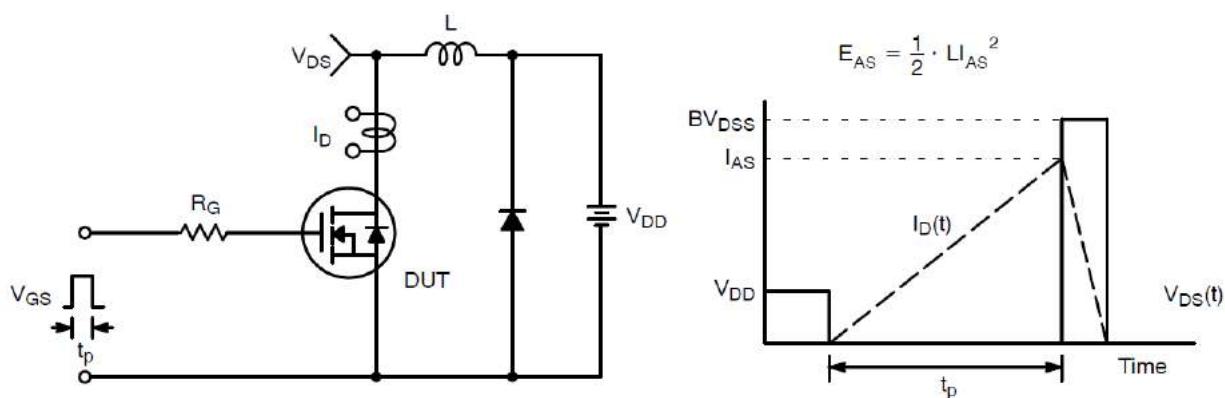
Test Circuit and Waveform:



Gate Charge Test Circuit & Waveform



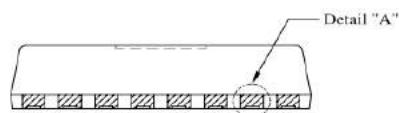
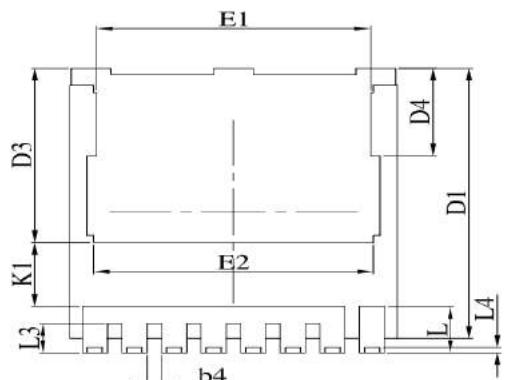
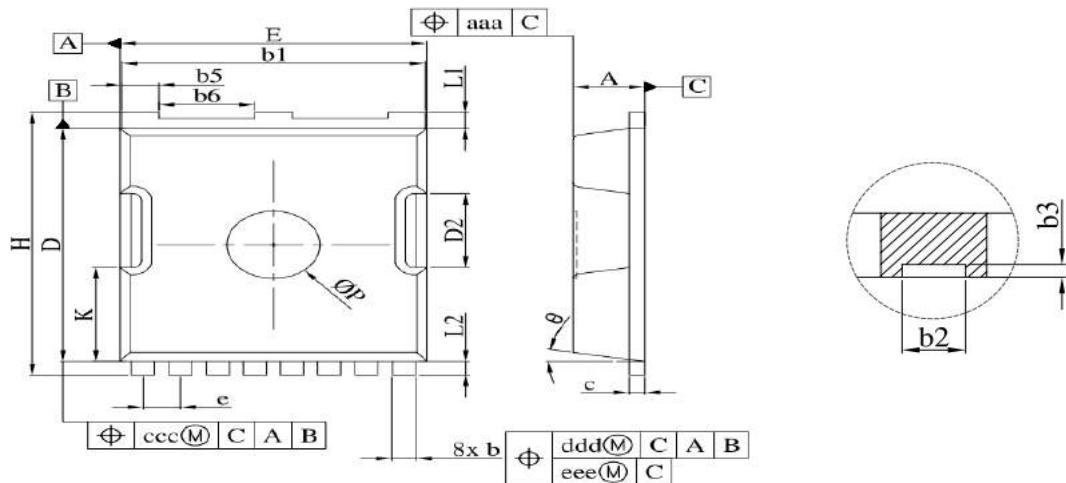
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



TOLL-8L Package Information



SYMBOL	COMMON		
	MILLIMETER		
	MIN.	NOMINAL	MAX.
A	2.20	2.30	2.40
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.36	0.45	0.55
b3	0.05	0.100	0.35
b4	0.30	0.40	0.50
b5	1.10	1.20	1.30
b6	3.00	3.10	3.20
c	0.40	0.50	0.60
D	10.28	10.38	10.55
D1	10.98	11.08	11.18
D2	3.20	3.30	3.40
D3	7.00	7.15	7.30
D4	3.44	3.59	3.74
e	1.10	1.20	1.30
E	9.80	9.90	10.00
E1	8.20	8.30	8.40
E2	8.35	8.50	8.65
H	11.50	11.68	11.85
K	4.08	4.18	4.28
K1	2.45	---	---
L	1.60	1.90	2.10
L1	0.50	0.70	0.90
L2	0.50	0.60	0.70
L3	1.00	1.20	1.30
L4	0.13	0.23	0.33
P	2.85	3.00	3.15
θ	10° REF		
aaa	0.20		
ccc	0.20		
ddd	0.25		
eee	0.20		

Customer Service

Sales and Service:

zj@ztasemi.com